	Application No.	Applicant(s)	
	10/686,788	ASANO ET AL.	
Notice of Allowability	Examiner	Art Unit	
	Steven H. Rao	2814	
The MAILING DATE of this communication apperall claims being allowable, PROSECUTION ON THE MERITS IS (herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT Re	(OR REMAINS) CLOSED or other appropriate comm GHTS. This application is	in this application. If not included nunication will be mailed in due course	
1. This communication is responsive to 6/21/2004.			-
2. 🔀 The allowed claim(s) is/are <u>1-35</u> .		·	
3. X The drawings filed on 17 October 2003 are accepted by the	e Examiner.		-
<ul> <li>4.  Acknowledgment is made of a claim for foreign priority un a)  All b)  Some* c)  None of the:</li> <li>1.  Certified copies of the priority documents have</li> <li>2.  Certified copies of the priority documents have</li> <li>3.  Copies of the certified copies of the priority documents have</li> <li>International Bureau (PCT Rule 17.2(a)).</li> </ul>	been received. been received in Application	on No	om the
* Certified copies not received:  Applicant has THREE MONTHS FROM THE "MAILING DATE" of noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.  5. A SUBSTITUTE OATH OR DECLARATION must be submit	ENT of this application.		
INFORMAL PATENT APPLICATION (PTO-152) which give	es reason(s) why the oath	or declaration is deficient.	
6. CORRECTED DRAWINGS ( as "replacement sheets") mus			
(a) including changes required by the Notice of Draftspers	on's Patent Drawing Revie	w ( PTO-948) attached	
1) hereto or 2) to Paper No./Mail Date		to the Office and are of	
(b) including changes required by the attached Examiner's Paper No./Mail Date	s Amenament / Comment o	or in the Office action of	
Identifying indicia such as the application number (see 37 CFR 1, each sheet. Replacement sheet(s) should be labeled as such in the	.84(c)) should be written on he header according to 37 C	the drawings in the front (not the back) FR 1.121(d).	of
7. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT I	SIT OF BIOLOGICAL MAT FOR THE DEPOSIT OF B	ERIAL must be submitted. Note the IOLOGICAL MATERIAL.	ne
Attachment(s)  1. ☑ Notice of References Cited (PTO-892)	<del></del>	nformal Patent Application (PTO-152)	)
2. Notice of Draftperson's Patent Drawing Review (PTO-948)		Summary (PTO-413), ./Mail Date	
<ul> <li>3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 2/23 &amp; 6/21/04</li> <li>4. ☐ Examiner's Comment Regarding Requirement for Deposit</li> </ul>	98), 7. ☐ Examiner'	s Amendment/Comment s Statement of Reasons for Allowance	е
of Biological Material	9. ☐ Other	<u>.</u>	

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## Allowable Subject Matter

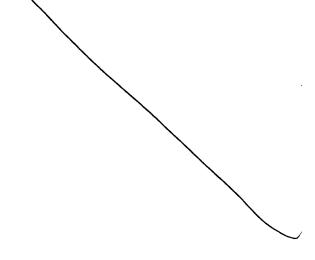
## **Priority**

Receipt is acknowledged of paper submitted under 35 U.S.C. 119(a)-(d), claiming priority from Japanese Patent Application No. 2002-303484 filed on October 17, 2002 and PCT/JP03/11419 filed on September 08, 2003 which papers have been placed of record in the file.

## Information Disclosure Statement

Acknowledgment is made of receipt of Applicant's Information Disclosure Statement (PTO-1449) filled on February 23, 2003 and June 21, 2004

The references on PTO 1499 submitted on 02/23/2003 and 06/21/2004 are acknowledged. All the cited references have been considered. However the foreign patents and documents cited by applicant are considered to the extent that could be understood from the abstract and drawings.



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## Reasons for allowance

Claims 1-35 are allowed.

The following is an examiner's statement of reasons for allowance:

The prior art taken either singularly or in combination fails to anticipate or fairly suggest the limitation of the dependent claims, in such manner that a rejection under 35 U.S.C. 102 or 103 would be proper. The prior art fails to teach a combination of all the claimed features as presented in independent claims, which include A switching circuit device comprising a substrate comprising an insulating region; a first field effect transistor, a second field effect transistor, a third field effect transistor and a fourth field transistor, each of the first, second, third and forth transistors comprising a source electrode, a gate electrode and a drain electrode; a common input terminal connected to the source electrodes or the drain electrodes of the first and second transistors; a first output terminal connected to the source electrode or the drain electrode of the first transistor, which is not connected to the common input terminal, and connected to the source electrode or the drain electrode of the third transistor; a second output terminal connected to the source electrode or the drain electrode of the second transistor, which is not connected to the common input terminal, and connected to the source electrode or the drain electrode of the fourth transistor; a first control terminal connected to the gate electrodes of the first and fourth transistors, a second control terminal connected to the gate electrodes of the second and third transistors; a highfrequency ground terminal connected to the source electrodes or the drain

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electrodes of the third and fourth transistors, which are not connected to the corresponding output terminals; and a protecting element comprising a first high concentration impurity region, a second high concentration impurity region and at least part of the insulating region of the substrate, said part of the insulating region being located between the first and second high concentration impurity regions, wherein the protecting element is connected between the first output terminal and the gate electrode of the third transistor or between the second output terminal and the gate electrode of the fourth transistor and is configured to discharge at least partially electrostatic energy of external origin through the protecting element so that the electrostatic energy is reduced enough not to provide an electrostatic breakdown voltage between the gate electrode and the corresponding source or drain electrode of the transistor that is connected to the protecting element.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Steven H. Rao whose telephone number is (703) 3065945. The examiner can normally be reached on 8.00 to 5.00.

. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR.

Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Steven H. Rao

Patent Examiner

December 09, 2004.

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